

ABSTRACT OF THE DISCLOSURE

A number of transistors including gate oxide films of different thicknesses and an external terminal are formed on a semiconductor substrate. The transistor connected directly to the external terminal is a transistor other than the transistor having the thinnest gate oxide film. That is, a node which is in contact with an external power supply and thus requires a high breakdown voltage is formed of a thick gate oxide film transistor, while a node which is not in contact with the external power supply is formed of a thin gate oxide film transistor. With this structure, a number of transistors including gate oxide films of different thicknesses can be integrated in a single chip without deterioration of the transistor characteristics. Hence, the degree of freedom with which to design devices/circuits can be remarkably enhanced.

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